

Silicon NPN Darlington Power Transistors

2SD2495

DESCRIPTION

- With TO-220F package
- Complement to type 2SB1626

APPLICATIONS

- For audio, series regulator and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

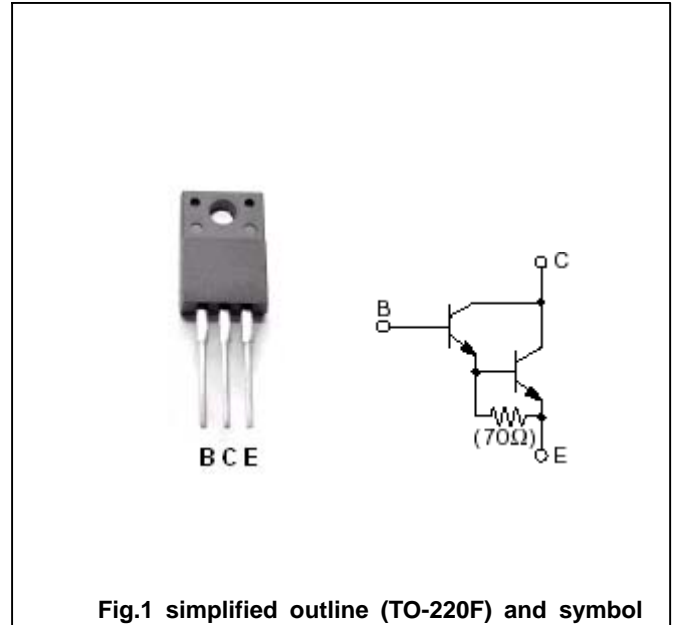


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25 °C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	Open emitter	110	V
V _{CEO}	Collector-emitter voltage	Open base	110	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		6	A
I _B	Base current		1	A
P _C	Collector dissipation	T _C =25	30	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	110			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =5mA			2.5	V
V _{BEsat}	Emitter-base saturation voltage	I _C =5A; I _B =5mA			3.0	V
I _{CBO}	Collector cut-off current	V _{CB} =110V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =4V	5000			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =12V		60		MHz
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =10V		55		pF

Switching times

t _{on}	Turn-on time	I _C =5A; I _{B1} =-I _{B2} =5mA V _{CC} =30V , R _L =6		0.8		μs
t _s	Storage time			6.2		μs
t _f	Fall time			1.1		μs

◆ h_{FE} Classifications

O	p	Y
5000-12000	6500-20000	15000-30000

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PACKAGE OUTLINE

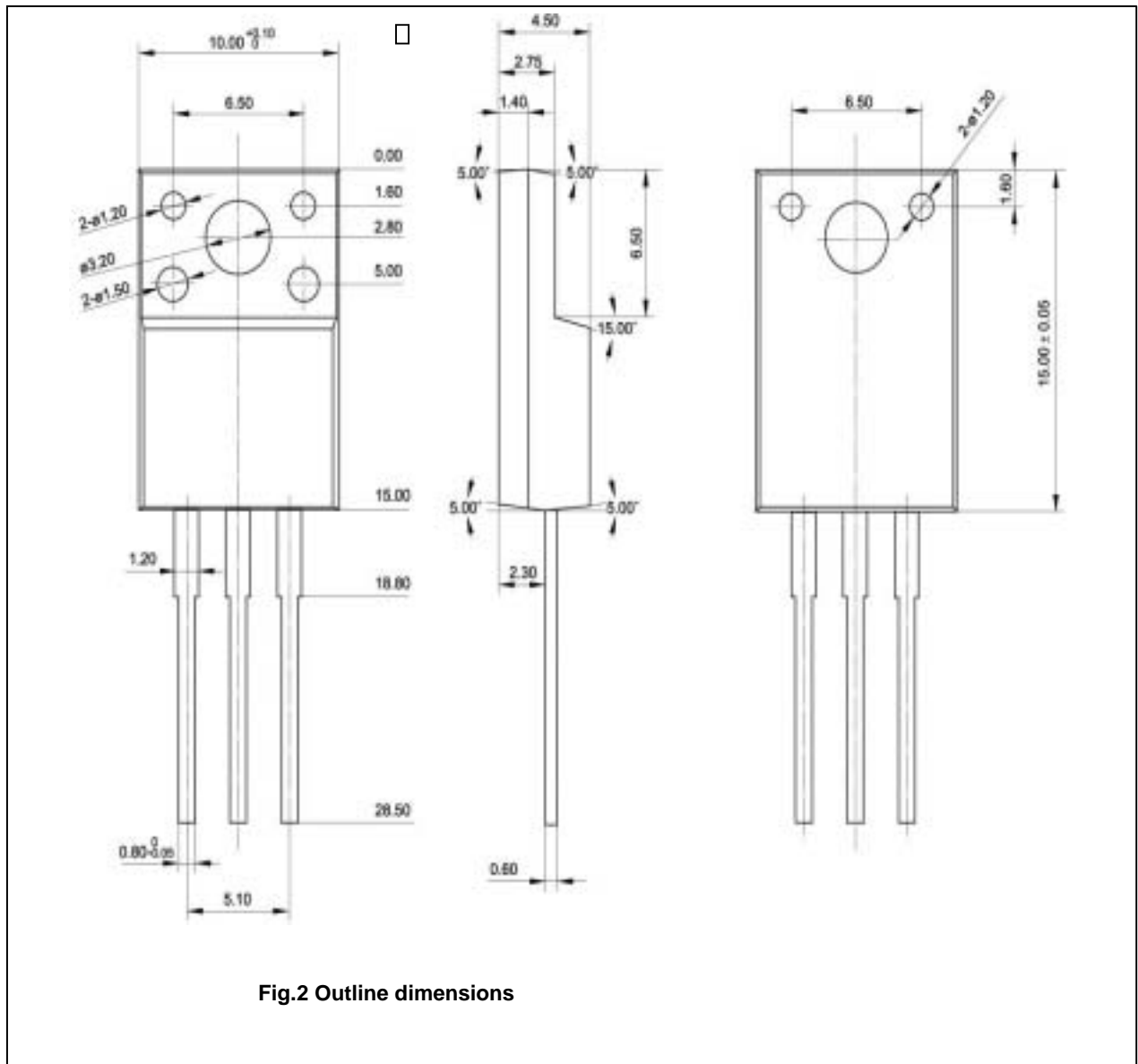


Fig.2 Outline dimensions